



1GB – 2x64Mx72 DDR2 SDRAM UDIMM, SO-DIMM w/PLL

FEATURES

- Unbuffered 200-pin (SO-DIMM) small-outline dual in-line memory module
- Support ECC detection and correction
- Fast data transfer rates: PC2-6400*, PC2-5300*, PC2-4200 and PC2-3200
- $V_{CC} = V_{CCQ} = 1.8V \pm 0.1V$
- $V_{CCSPD} = 1.7V$ to $3.6V$
- JEDEC standard 1.8V I/O (SSTL_18-compatible)
- Differential data strobe (DQS, DQS#) option
- Differential clock input (CK, CK#)
- Four-bit prefetch architecture
- Multiple internal device banks for concurrent operation
- Programmable CAS# latency (CL): 3 4, 5*, and 6*
- Adjustable data-output drive strength
- 7.8 μ s average periodic refresh interval
- On-die termination (ODT)
- Posted CAS# latency: 0, 1, 2, 3 and 4
- Serial Presence Detect (SPD) with EEPROM
- Auto & self refresh (64ms: 8,192 cycle refresh)
- Gold edge contacts
- Dual Rank
- RoHS compliant
- JEDEC proposed pin-out
- Package option
 - 200 Pin SO-DIMM: 30.00mm (1.181") TYP

DESCRIPTION

The WV3HG264M72EEU is a 2x64Mx72 Double Data Rate DDR2 SDRAM high density module. This memory module consists of eighteen 64Mx8 bit DDR2 Synchronous DRAMs in FBGA packages, mounted on a 200-pin SO-DIMM FR4 substrate.

* This product is under development, is not qualified or characterized and is subject to change or cancellation without notice.

NOTE: Consult factory for availability of:

- Vendor source control options
- Industrial temperature option

OPERATING FREQUENCIES

	PC2-3200	PC2-4200	PC2-5300*	PC2-6400*
Clock Speed	200MHz	266MHz	333MHz	400MHz
CL-tRCD-tRP	3-3-3	4-4-4	5-5-5	6-6-6

* Consult factory for availability



PIN CONFIGURATION

Pin No.	Symbol	Pin No.	Symbol	Pin No.	Symbol	Pin No.	Symbol
1	V _{REF}	51	DQ18	101	V _{CC}	151	V _{SS}
2	V _{SS}	52	V _{SS}	102	A6	152	V _{SS}
3	DQ0	53	DQ19	103	A5	153	DQS5#
4	DQ4	54	DQ28	104	A4	154	DM5
5	V _{SS}	55	V _{SS}	105	A3	155	DQS5
6	DQ5	56	DQ29	106	V _{CC}	156	V _{SS}
7	DQ1	57	DQ24	107	A2	157	V _{SS}
8	V _{SS}	58	V _{SS}	108	A1	158	DQ46
9	DQS0#	59	DQ25	109	V _{CC}	159	DQ42
10	DM0	60	DM3	110	A0	160	DQ47
11	DQS0	61	V _{SS}	111	A10/AP	161	DQ43
12	V _{SS}	62	V _{SS}	112	BA1	162	V _{SS}
13	V _{SS}	63	DQS3#	113	BA0	163	V _{SS}
14	DQ6	64	DQ30	114	V _{CC}	164	DQ52
15	DQ2	65	DQS3	115	RAS#	165	DQ48
16	DQ7	66	DQ31	116	WE#	166	DQ53
17	DQ3	67	V _{SS}	117	V _{CC}	167	DQ49
18	V _{SS}	68	V _{SS}	118	CS0#	168	V _{SS}
19	V _{SS}	69	DQ26	119	CAS#	169	V _{SS}
20	DQ12	70	CB4	120	ODT0	170	DM6
21	DQ8	71	DQ27	121	CS1#	171	DQS6#
22	DQ13	72	CB5	122	A13	172	V _{SS}
23	DQ9	73	V _{SS}	123	V _{CC}	173	DQS6
24	V _{SS}	74	V _{SS}	124	V _{CC}	174	DQ54
25	V _{SS}	75	CB0	125	ODT1	175	V _{SS}
26	DM1	76	DM8	126	CK	176	DQ55
27	DQS1#	77	CB1	127	NC	177	DQ50
28	V _{SS}	78	V _{SS}	128	CK#	178	V _{SS}
29	DQS1	79	V _{SS}	129	DQ32	179	DQ51
30	DQ14	80	CB6	130	V _{SS}	180	DQ60
31	V _{SS}	81	DQS8#	131	V _{SS}	181	V _{SS}
32	DQ15	82	CB7	132	DQ36	182	DQ61
33	DQ10	83	DQS8	133	DQ33	183	DQ56
34	V _{SS}	84	V _{SS}	134	DQ37	184	V _{SS}
35	DQ11	85	V _{SS}	135	DQS4#	185	DQ57
36	DQ20	86	CB2	136	V _{SS}	186	DM7
37	V _{SS}	87	CKE0	137	DQS4	187	V _{SS}
38	DQ21	88	CB3	138	DM4	188	DQ62
39	DQ16	89	NC	139	V _{SS}	189	DQS7#
40	V _{SS}	90	V _{SS}	140	V _{SS}	190	V _{SS}
41	DQ17	91	NC	141	DQ34	191	DQS7
42	RESET#	92	NC	142	DQ38	192	DQ63
43	V _{SS}	93	V _{CC}	143	DQ35	193	DQ58
44	DM2	94	NC	144	DQ39	194	SDA
45	DQS2#	95	A12	145	V _{SS}	195	V _{SS}
46	V _{SS}	96	A11	146	V _{SS}	196	SCL
47	DQS2	97	A9	147	DQ40	197	DQ59
48	DQ22	98	V _{CC}	148	DQ44	198	SA1
49	V _{SS}	99	A7	149	DQ41	199	VCCSPD
50	DQ23	100	A8	150	DQ45	200	SA0

PIN NAMES

Pin Name	Function
A0-A13	Address Inputs
BA0, BA1	SDRAM Bank Address
DQ0-DQ63	Data Input/Output
CB0-CB7	Check Bits
DQS0-DQS8	Data strobes
DQS0#-DQS8#	Data strobes complement
ODT0, ODT1	On-die termination controls
CK, CK#	Clock inputs
CKE0, CKE1	Clock enable inputs
CS0#, CS1#	Chip select inputs
RAS#	Row Address Strobe
CAS#	Column Address Strobe
WE#	Write Enable
RESET#	Register reset input
V _{CC}	Core Power
V _{SS}	Ground
SA0-SA1	SPD address
SDA	Serial Data Input/Output
V _{REF}	Input/Output Reference Voltage
DM0-DM8	Data-in mask
V _{CCSPD}	Serial EEPROM power supply
SCL	SPD Clock Input
NC	No connect



NOTE: All resistor values are 22 ohms unless otherwise specified.



DC OPERATING CONDITIONS

All voltages referenced to V_{SS}

Parameter	Symbol	Min	Typical	Max	Unit	Notes
Supply Voltage	V _{CC}	1.7	1.8	1.9	V	3
I/O Reference Voltage	V _{REF}	0.49 x V _{CC}	0.50 x V _{CC}	0.51 x V _{CC}	V	1
I/O Termination Voltage	V _{TT}	V _{REF} -0.04	V _{REF}	V _{REF} +0.04	V	2
SPD Supply Voltage	V _{CCSPD}	1.7	-	3.6	V	

Notes:

- 1 V_{REF} is expected to equal V_{CC}/2 of the transmitting device and to track variations in the DC level of the same. Peak-to-peak noise on V_{REF} may not exceed +/-1 percent of the DC value. Peak-to-peak AC noise on V_{REF} may not exceed +/-2 percent of V_{REF}. This measurement is to be taken at the nearest V_{REF} bypass capacitor.
- 2 V_{TT} is not applied directly to the device. V_{TT} is a system supply for signal termination resistors, is expected to be set equal to V_{REF} and must track variations in the DC level of V_{REF}.
- 3 V_{CCQ} of all IC's are tied to V_{CC}.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Min	Max	Units
V _{CC}	Voltage on V _{CC} pin relative to V _{SS}		-0.5	2.3	V
V _{IN} , V _{OUT}	Voltage on any pin relative to V _{SS}		-0.5	2.3	V
I _L	Input leakage current; Any input 0V<V _{IN} <V _{CC} ; V _{REF} input 0V,V _{IN} ,0.95V; Other pins not under test = 0V	Command/Address, RAS#, CAS#, WE#,	-90	90	μA
		CS#, CKE	-45	45	μA
		CK, CK#	-10	10	μA
		DM	-10	10	μA
I _{OZ}	Output leakage current; 0V<V _{IN} <V _{CC} ; DQs and ODT are disable	DQ, DQS, DQS#	-10	10	μA
I _{VREF}	V _{REF} leakage current; V _{REF} = Valid V _{REF} level		-36	36	μA

INPUT/OUTPUT CAPACITANCE

TA=25°C, f=100MHz

Parameter	Symbol	Min	Max	Unit
Input capacitance (0A~A13, BA0~BA1, RAS#, CAS#, WE#)	C _{IN1}	22	40	pF
Input capacitance (CKE0, CKE1), (ODT0, ODT1)	C _{IN2}	13	22	pF
Input capacitance (CS0# - CS1#)	C _{IN3}	13	22	pF
Input capacitance (CK, CK#)	C _{IN4}	6	7	pF
Input capacitance (DM0~DM8), (DQS0~DQS8)	C _{IN5} (665)	9	11	pF
	C _{IN5} (534, 403)	9	12	pF
Input capacitance (DQ0~DQ63), (CB0~CB7)	C _{OUT1} (665)	9	11	pF
	C _{OUT1} (534, 403)	9	12	pF

**OPERATING TEMPERATURE CONDITION**

Parameter	Symbol	Rating	Units	Notes
Operating temperature (Commercial)	TOPER	0° to 85°	°C	1, 2

Notes:

- Operating temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JEDED JESD51.2
- At 0°C - 85°C, operation temperature range, all DRAM specification will be supported.

INPUT DC LOGIC LEVELAll voltages referenced to V_{SS}

Parameter	Symbol	Min	Max	Units
Input High (Logic 1) Voltage	$V_{IH}(DC)$	$V_{REF} + 0.125$	$V_{CC} + 0.300$	V
Input Low (Logic 0) Voltage	$V_{IL}(DC)$	-0.300	$V_{REF} - 0.125$	V

INPUT AC LOGIC LEVELAll voltages referenced to V_{SS}

Parameter	Symbol	Min	Max	Unit
AC Input High (Logic 1) Voltage DDR2-400 & DDR2-533	$V_{IH}(AC)$	$V_{REF} + 0.250$	-	V
AC Input High (Logic 1) Voltage DDR2-667	$V_{IH}(AC)$	$V_{REF} + 0.200$	-	V
AC Input High (Logic 0) Voltage DDR2-400 & DDR2-533	$V_{IL}(AC)$	-	$V_{REF} - 0.250$	V
AC Input High (Logic 0) Voltage DDR2-667	$V_{IL}(AC)$	-	$V_{REF} - 0.200$	V

DDR2 I_{cc} SPECIFICATIONS AND CONDITIONS

Includes DDR2 SDRAM components only

V_{CC} = +1.8V ± 0.1V

Symbol	Proposed Conditions	806	665	534	403	Units
I _{CC0} *	Operating one bank active-precharge current; t _{CK} = t _{CK} (I _{CC}), t _{RC} = t _{RC} (I _{CC}), t _{RAS} = t _{RASmin} (I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	TBD	1,137	1,092	1,092	mA
I _{CC1} *	Operating one bank active-read-precharge current; I _{OUT} = 0mA; BL = 4, CL = CL(I _{CC}), AL = 0; t _{CK} = t _{CK} (I _{CC}), t _{RC} = t _{RC} (I _{CC}), t _{RAS} = t _{RASmin} (I _{CC}), t _{RCD} = t _{RCD} (I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as I _{CC4W}	TBD	1,272	1,227	1,227	mA
I _{CC2P} *	Precharge power-down current; All banks idle; t _{CK} = t _{CK} (I _{CC}); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	TBD	444	444	444	mA
I _{CC2Q} **	Precharge quiet standby current; All banks idle; t _{CK} = t _{CK} (I _{CC}); CKE is HIGH, CS# is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	TBD	930	840	840	mA
I _{CC2N} **	Precharge standby current; All banks idle; t _{CK} = t _{CK} (I _{CC}); CKE is HIGH, CS# is HIGH; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	TBD	1,020	930	930	mA
I _{CC3P} **	Active power-down current; All banks open; t _{CK} = t _{CK} (I _{CC}); CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	Fast PDN Exit MRS(12) = 0	TBD	840	840	mA
		Slow PDN Exit MRS(12) = 1	TBD	516	516	mA
I _{CC3N} **	Active standby current; All banks open; t _{CK} = t _{CK} (I _{CC}), t _{RAS} = t _{RASmax} (I _{CC}), t _{RP} = t _{RP} (I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	TBD	1,290	1,200	1,200	mA
I _{CC4W} *	Operating burst write current; All banks open, Continuous burst writes; BL = 4, CL = CL(I _{CC}), AL = 0; t _{CK} = t _{CK} (I _{CC}), t _{RAS} = t _{RASmax} (I _{CC}), t _{RP} = t _{RP} (I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING	TBD	1,632	1,452	1,362	mA
I _{CC4R} *	Operating burst read current; All banks open, Continuous burst reads, I _{OUT} = 0mA; BL = 4, CL = CL(I _{CC}), AL = 0; t _{CK} = t _{CK} (I _{CC}), t _{RAS} = t _{RASmax} (I _{CC}), t _{RP} = t _{RP} (I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as I _{CC4W}	TBD	1,677	1,497	1,362	mA
I _{CC5B} **	Burst auto refresh current; t _{CK} = t _{CK} (I _{CC}); Refresh command at every t _{REFC} (I _{CC}) interval; CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING	TBD	3,000	2,820	2,820	mA
I _{CC6} **	Self refresh current; CK and CK# at 0V; CKE 0.2V; Other control and address bus inputs are FLOATING; Data bus inputs are FLOATING	Normal	TBD	144	144	mA
I _{CC7} *	Operating bank interleave read current; All bank interleaving reads, I _{OUT} = 0mA; BL = 4, CL = CL(I _{CC}), AL = t _{RCD} (I _{CC})-1*t _{CK} (I _{CC}); t _{CK} = t _{CK} (I _{CC}), t _{RC} = t _{RC} (I _{CC}), t _{RRD} = t _{RRD} (I _{CC}), t _{RCD} = 1*t _{CK} (I _{CC}); CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are STABLE during DESELECTs; Data bus inputs are SWITCHING.	TBD	2,352	2,352	2,352	mA

I_{CC} specification is based on **SAMSUNG** components. Other DRAM manufactures specification may be different.

Note:

* Value calculated as one module rank in this operating condition, and all other module ranks in I_{CC2P} (CKE LOW) mode.

** Value calculated reflects all module ranks in this operating condition.



AC TIMING PARAMETERS & SPECIFICATIONS

V_{CC} = +1.8V ± 0.1V

AC CHARACTERISTICS				806		665		534		403		
PARAMETER			SYMBOL	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Clock	Clock cycle time	CL = 6	t _{CK} (6)	TBD	TBD							ps
		CL = 5	t _{CK} (5)	TBD	TBD	3,000	8,000					ps
		CL = 4	t _{CK} (4)	TBD	TBD	3,750	8,000	3,750	8,000	5,000	8,000	ps
		CL = 3	t _{CK} (3)	TBD	TBD	5,000	8,000	5,000	8,000	5,000	8,000	ps
	CK high-level width		t _{CH}	TBD	TBD	0.45	0.55	0.45	0.55	0.45	0.55	t _{CK}
	CK low-level width		t _{CL}	TBD	TBD	0.45	0.55	0.45	0.55	0.45	0.55	t _{CK}
	Half clock period		t _{HP}	TBD	TBD	MIN(t _{CH} , t _{CL})		MIN(t _{CH} , t _{CL})		MIN(t _{CH} , t _{CL})		ps
	Clock jitter		t _{JIT}	TBD	TBD	-125	125	-125	125	-125	125	ps
Data	DQ output access time from CK/CK#		t _{AC}	TBD	TBD	-450	+450	-500	+500	-600	+600	ps
	Data-out high-impedance window from CK/CK#		t _{HZ}	TBD	TBD		t _{AC} (MAX)		t _{AC} (MAX)		t _{AC} (MAX)	ps
	Data-out low-impedance window from CK/CK#		t _{LZ}	TBD	TBD	t _{AC} (MIN)	t _{AC} (MAX)	t _{AC} (MIN)	t _{AC} (MAX)	t _{AC} (MIN)	t _{AC} (MAX)	ps
	DQ and DM input setup time relative to DQS		t _{DS}	TBD	TBD	100		100		150		
	DQ and DM input hold time relative to DQS		t _{DH}	TBD	TBD	225		225		275		
	DQ and DM input pulse width (for each input)		t _{OLPW}	TBD	TBD	0.35		0.35		0.35		t _{CK}
	Data hold skew factor		t _{QHS}	TBD	TBD		340		400		450	ps
	DQ...DQS hold, DQS to first DQ to go nonvalid, per access		t _{QH}	TBD	TBD	t _{HP} - t _{QHS}		t _{HP} - t _{QHS}		t _{HP} - t _{QHS}		ps
	Data valid output window (DVW)		t _{DVW}	TBD	TBD	t _{QH} - t _{DQSQ}		t _{QH} - t _{DQSQ}		t _{QH} - t _{DQSQ}		ns
Data Strobe	DQS input high pulse width		t _{DQSH}	TBD	TBD	0.35		0.35		0.35		t _{CK}
	DQS input low pulse width		t _{DQSL}	TBD	TBD	0.35		0.35		0.35		t _{CK}
	DQS output access time from CK/CK#		t _{DQSCK}	TBD	TBD	-400	+400	-450	+450	-500	+500	ps
	DQS falling edge to CK rising ... setup time		t _{DSS}	TBD	TBD	0.2		0.2		0.2		t _{CK}
	DQS falling edge from CK rising ... hold time		t _{DSH}	TBD	TBD	0.2		0.2		0.2		t _{CK}
	DQS...DQ skew, DQS to last DQ valid, per group, per access		t _{DQSQ}	TBD	TBD		240		300		350	ps
	DQS read preamble		t _{RPRE}	TBD	TBD	0.9	1.1	0.9	1.1	0.9	1.1	t _{CK}
	DQS read postamble		t _{RPST}	TBD	TBD	0.4	0.6	0.4	0.6	0.4	0.6	t _{CK}
	DQS write preamble setup time		t _{WPRES}	TBD	TBD	0		0		0		ps
	DQS write preamble		t _{WPRE}	TBD	TBD	0.35		0.35		0.35		t _{CK}
	DQS write postamble		t _{WPST}	TBD	TBD	0.4	0.6	0.4	0.6	0.4	0.6	t _{CK}
	Write command to first DQS latching transition		t _{DQSS}	TBD	TBD	WL- 0.25	WL+ 0.25	WL- 0.25	WL+ 0.25	WL- 0.25	WL+ 0.25	t _{CK}
	Address and control input pulse width for each input		t _{IPW}	TBD	TBD	0.6		0.6		0.6		t _{CK}
	Address and control input setup time		t _{IS}	TBD	TBD	200		250		250		ps
	Address and control input hold time		t _{IH}	TBD	TBD	275		375		475		ps
	Address and control input hold time		t _{CCD}	TBD	TBD	2		2		2		t _{CK}

* AC specification is based on **SAMSUNG** components. Other DRAM manufactures specification may be different.

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AC TIMING PARAMETERS & SPECIFICATIONS (cont'd)

V_{CC} = +1.8V ± 0.1V

AC CHARACTERISTICS			806		665		534		403		
PARAMETER		SYMBOL	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Command and Address	ACTIVE to ACTIVE (same bank) command	t _{RC}	TBD	TBD	55		55		55		ns
	ACTIVE bank a to ACTIVE bank b command	t _{RRD}	TBD	TBD	7.5		7.5		7.5		ns
	ACTIVE to READ or WRITE delay	t _{RCD}	TBD	TBD	15		15		15		ns
	Four Bank Activate period	t _{FAW}	TBD	TBD	37.5	37.5	37.5	37.5	37.5	37.5	ns
	ACTIVE to PRECHARGE command	t _{RAS}	TBD	TBD	45	70,000	45	70,000	45	70,000	ns
	Internal READ to precharge command delay	t _{RTP}	TBD	TBD	7.5		7.5		7.5		ns
	Write recovery time	t _{WR}	TBD	TBD	15		15		15		ns
	Auto precharge write recovery + precharge time	t _{DAL}	TBD	TBD	t _{WR} + t _{RP}		t _{WR} + t _{RP}		t _{WR} + t _{RP}		ns
	Internal WRITE to READ command delay	t _{WTR}	TBD	TBD	7.5		7.5		10		ns
	PRECHARGE command period	t _{RP}	TBD	TBD	15		15		15		ns
	PRECHARGE ALL command period	t _{RPA}	TBD	TBD	t _{RP} + t _{CK}		t _{RP} + t _{CK}		t _{RP} + t _{CK}		ns
	LOAD MODE command cycle time	t _{M RD}	TBD	TBD	2		2		2		t _{CK}
	CKE low to CK, CK# uncertainty	t _{DELAY}	TBD	TBD	t _{IS} + t _{CK} + t _{IH}		t _{IS} + t _{CK} + t _{IH}		t _{IS} + t _{CK} + t _{IH}		ns
Self Refresh	REFRESH to Active of Refresh to Refresh command interfal	t _{RFC}	TBD	TBD	105	70,000	105	70,000	105	70,000	ns
	Average periodic refresh interval	t _{REFI}	TBD	TBD		7.8		7.8		7.8	μs
	Exit self refresh to non-READ command	t _{XSNR}	TBD	TBD	t _{RFC} (MIN) + 10		t _{RFC} (MIN) + 10		t _{RFC} (MIN) + 10		ns
	Exit self refresh to READ command	t _{XSRD}	TBD	TBD	200		200		200		t _{CK}
	Exit self refresh timing reference	t _{ISXR}	TBD	TBD	t _{IS}		t _{IS}		t _{IS}		ps
ODT	ODT turn-on delay	t _{AOND}	TBD	TBD	2	2	2	2	2	2	t _{CK}
	ODT turn-on	t _{AON}	TBD	TBD	t _{tAC} (MIN)	t _{tAC} (MAX) + 1000	t _{tAC} (MIN)	t _{tAC} (MAX) + 1000	t _{tAC} (MIN)	t _{tAC} (MAX) + 1000	ps
	ODT turn-off delay	t _{AOFD}	TBD	TBD	2.5	2.5	2.5	2.5	2.5	2.5	t _{CK}
	ODT turn-off	t _{AOF}	TBD	TBD	t _{tAC} (MIN)	t _{tAC} (MAX) + 600	t _{tAC} (MIN)	t _{tAC} (MAX) + 600	t _{tAC} (MIN)	t _{tAC} (MAX) + 600	ps
	ODT turn-on (power-down mode)	t _{AONPD}	TBD	TBD	t _{tAC} (MIN) + 2000	2 x t _{CK} + t _{tAC} (MAX) + 1000	t _{tAC} (MIN) + 2000	2 x t _{CK} + t _{tAC} (MAX) + 1000	t _{tAC} (MIN) + 2000	2 x t _{CK} + t _{tAC} (MAX) + 1000	ps
	ODT turn-off (power-down mode)	t _{AOFPD}	TBD	TBD	t _{tAC} (MIN) + 2000	2.5 x t _{CK} + t _{tAC} (MAX) + 1000	t _{tAC} (MIN) + 2000	2.5 x t _{CK} + t _{tAC} (MAX) + 1000	t _{tAC} (MIN) + 2000	2.5 x t _{CK} + t _{tAC} (MAX) + 1000	ps
	ODT to power-down entry latency	t _{ANPD}	TBD	TBD	3		3		3		t _{CK}
	ODT power-down exit latency	t _{AXPD}	TBD	TBD	8		8		8		t _{CK}
Power-Down	Exit active power-down to READ command, MR[bit12=0]	t _{XARD}	TBD	TBD	2		2		2		t _{CK}
	Exit active power-down to READ command, MR[bit12=1]	t _{XARDS}	TBD	TBD	7 - AL		6 - AL		6 - AL		t _{CK}
	A Exit precharge power-down to any non-READ command.	t _{XP}	TBD	TBD	2		2		2		t _{CK}
	CKE minimum high/low time	t _{CKE}	TBD	TBD	3		3		3		t _{CK}

* AC specification is based on **SAMSUNG** components. Other DRAM manufactures specification may be different.

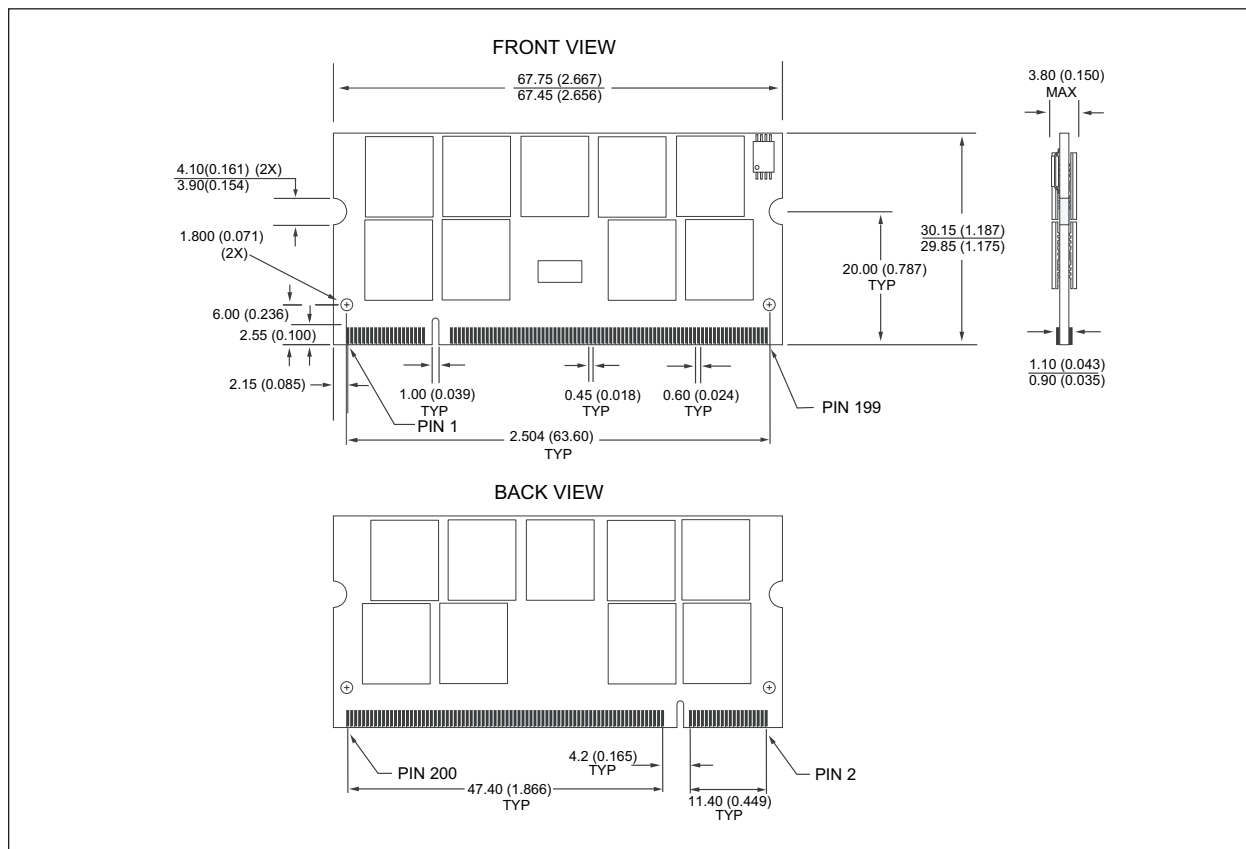
**ORDERING INFORMATION FOR PD4**

Part Number	Speed/Data Rate	CAS Latency	t _{RCD}	t _{RP}	Height*
WV3HG264M72EEU806PD4xxG**	400MHz/800Mb/s	6	6	6	30.00mm (1.81")TYP
WV3HG264M72EEU665PD4xxG**	333MHz/667Mb/s	5	5	5	30.00mm (1.81")TYP
WV3HG264M72EEU534PD4xxG	266MHz/533Mb/s	4	4	4	30.00mm (1.81")TYP
WV3HG264M72EEU403PD4xxG	200MHz/400Mb/s	3	3	3	30.00mm (1.81")TYP

** Consult factory for availability

NOTES:

- RoHS product. ("G" = RoHS Compliant)
- Vendor specific part numbers are used to provide memory component source control. The place holder for this is shown as a lower case "x" in the part numbers above and is to be replaced with respective vendors code. Consult factory for qualified sourcing options.
(M = Micron, S = Samsung & consult factory for others)

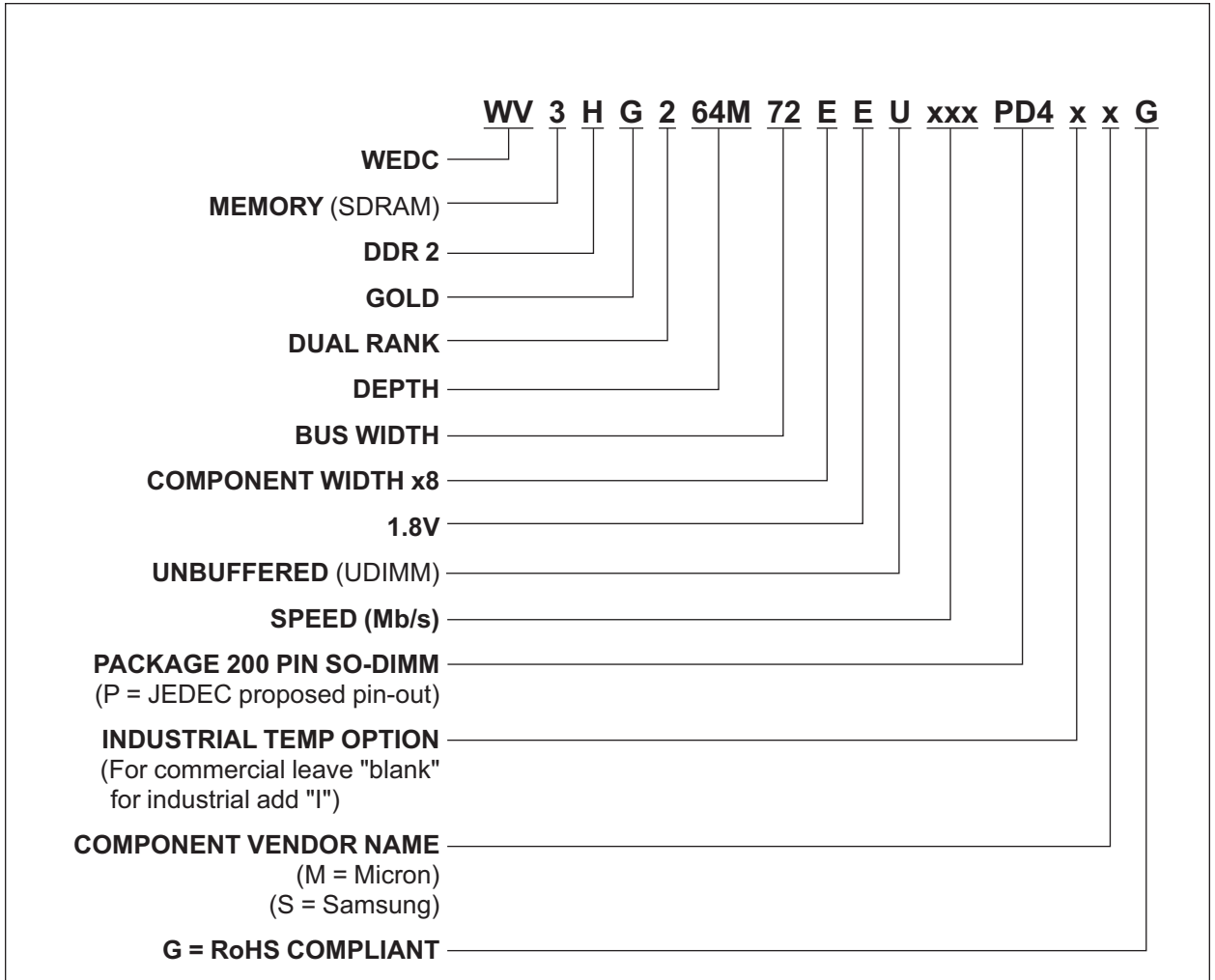
PACKAGE DIMENSIONS FOR PD4

* ALL DIMENSIONS ARE IN MILLIMETERS AND (INCHES)

Tolerances: ±0.13 (0.005) unless otherwise specified



PART NUMBERING GUIDE



**Document Title**

1GB – 2x64Mx72 DDR2 SDRAM UNBUFFERED, SO-DIMM w/PLL

DRAM DIE OPTIONS:

- SAMSUNG: C-Die, will move to E-Die Q2'06
- MICRON: U37Y: B-Die

Revision History

Rev #	History	Release Date	Status
Rev 0	Created	August 2005	Concept
Rev 1	1.0 Updated Icc, CAP & AC specs 1.1 Added industrial temp option to part numbering guide 1.2 Changed from concept to advanced	March 2006	Advanced
Rev 2	2.0 Update Icc, CAP & AC specs 2.1 Added "P" for JEDEC proposed pin-out 2.2 Added die Rev info	April 2006	Advanced